February 1992 Revised June 2001 74LVQ241 Low Voltage Octal Buffer/Line Driver with 3-STATE Outputs

FAIRCHILD

SEMICONDUCTOR TM

74LVQ241 Low Voltage Octal Buffer/Line Driver with 3-STATE Outputs

General Description

The LVQ241 is an octal buffer and line driver designed to be employed as a memory address driver, clock driver and bus oriented transmitter or receiver which provides improved PC board density.

Features

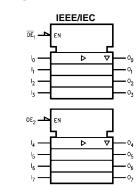
- Ideal for low power/low noise 3.3V applications
- Implements patented EMI reduction circuitry
- Available in SOIC JEDEC, SOIC EIAJ and QSOP packages
- Guaranteed simultaneous switching noise level and dynamic threshold performance
- Improved latch-up immunity
- \blacksquare Guaranteed incident wave switching into 75 $\!\Omega$
- 4 kV minimum ESD immunity

Ordering Code:

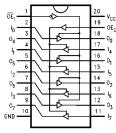
Order Number	Package Number	Package Description
74LVQ241SC	M20B	20-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-013, 0.300" Wide
74LVQ241SJ	M20D	20-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
74LVQ241QSC	MQA20	20-Lead Quarter Size Outline Package (QSOP), JEDEC MO-137, 0.150" Wide

Device also available in Tape and Reel. Specify by appending suffix letter "X" to the ordering code.

Logic Diagram



Connection Diagram



Truth Tables

inp	outs	Outputs			
OE ₁	I _n	(Pins 12, 14, 16, 18)			
L	L	L			
L	н	Н			
Н	Х	Z			
Inp	outs	Outputs			
OE ₂	I _n	(Pins 3, 5, 7, 9)			
L	Х	Z			
-		н			
H	Н	Н			

Pin Descriptions

Pin Names	Description
\overline{OE}_1 , OE_2	3-STATE Output Enable Inputs
OE ₁ , OE ₂ I ₀ –I ₇	Inputs
O ₀ O ₇	Outputs

Absolute Maximum Ratings(Note 1)

Supply Voltage (V _{CC})	-0.5V to +7.0V
DC Input Diode Current (IIK)	
$V_{I} = -0.5V$	–20 mA
$V_I = V_{CC} + 0.5V$	+20 mA
DC Input Voltage (VI)	–0.5V to V _{CC} + 0.5V
DC Output Diode Current (I _{OK})	
$V_{O} = -0.5V$	–20 mA
$V_{O} = V_{CC} + 0.5V$	+20 mA
DC Output Voltage (V _O)	–0.5V to V _{CC} + 0.5V
DC Output Source	
or Sink Current (I _O)	±50 mA
DC V _{CC} or Ground Current	
(I _{CC} or I _{GND})	±400 mA
Storage Temperature (T _{STG})	-65°C to +150°C
DC Latch-Up Source or	
Sink Current	±300 mA

Recommended Operating Conditions (Note 2)

Supply Voltage (V _{CC})	2.0V to 3.6V
Input Voltage (V _I)	0V to V _{CC}
Output Voltage (V _O)	0V to V_{CC}
Operating Temperature (T _A)	$-40^{\circ}C$ to $+85^{\circ}C$
Minimum Input Edge Rate $\Delta V/\Delta t$	
V _{IN} 0.8V to 2.0V	
V _{CC} @ 3.0V	125 mV/ns

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the Electrical Characteristics tables are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation

Note 2: Unused inputs must be held HIGH or LOW. They may not float.

DC Electrical Characteristics

Symbol	Parameter	V_{CC} $T_A = +25^{\circ}C$		+25°C	$T_A = -40^{\circ}C$ to $+85^{\circ}C$	Units	Conditions	
		(V)	Тур	Guaranteed Limits		Units	Conditions	
V _{IH}	Minimum High Level Input Voltage	3.0	1.5	2.0	2.0	V	$V_{OUT} = 0.1V$ or $V_{CC} - 0.1V$	
V _{IL}	Maximum Low Level Input Voltage	3.0	1.5	0.8	0.8	V	$V_{OUT} = 0.1V$ or $V_{CC} - 0.1V$	
V _{OH}	Minimum High Level	3.0	2.99	2.9	2.9	V	I _{OUT} = -50 μA	
	Output Voltage	3.0		2.58	2.48	V	$V_{IN} = V_{IL} \text{ or } V_{IH} \text{ (Note 3)}$ $I_{OH} = -12 \text{ mA}$	
V _{OL}	Maximum Low Level	3.0	0.002	0.1	0.1	V	I _{OUT} = 50 μA	
	Output Voltage	3.0		0.36	0.44	V	$V_{IN} = V_{IL} \text{ or } V_{IH} \text{ (Note 3)}$ $I_{OL} = 12 \text{ mA}$	
I _{IN}	Maximum Input Leakage Current	3.6		±0.1	±1.0	μA	V _I = V _{CC} , GND	
I _{OLD}	Minimum Dynamic	3.6			36	mA	V _{OLD} = 0.8V Max (Note 5)	
I _{OHD}	Output Current (Note 4)	3.6			-25	mA	V _{OHD} = 2.0V Min (Note 5)	
I _{CC}	Maximum Quiescent Supply Current	3.6		4.0	40.0	μA	V _{IN} = V _{CC} or GND	
I _{OZ}	Maximum 3-STATE Leakage Current	3.6		±0.25	±2.5	μΑ	$V_{I} (OE) = V_{IL}, V_{IH}$ $V_{I} = V_{CC}, GND$ $V_{O} = V_{CC}, GND$	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	3.3	0.4	0.8		V	(Note 6)(Note 7)	
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	3.3	-0.4	-0.8		V	(Note 6)(Note 7)	
V _{IHD}	Maximum High Level Dynamic Input Voltage	3.3	1.6	2.0		V	(Note 6)(Note 8)	
V _{ILD}	Maximum Low Level Dynamic Input Voltage	3.3	1.6	0.8		V	(Note 6)(Note 8)	

Note 3: All outputs loaded; thresholds on input associated with output under test.

Note 4: Maximum test duration 2.0 ms, one output loaded at a time.

Note 5: Incident wave switching on transmission lines with impedances as low as 75Ω for commercial temperature range is guaranteed for 74LVQ. Note 6: Worst case package.

Note 7: Max number of outputs defined as (n). Data Inputs are driven 0V to 3.3V. One output @ GND.

Note 8: Max number of Data Inputs (n) switching. n-1 Inputs switching 0V to 3.3V. Input-under-test switching: 3.3V to threshold (V_{ILD}), 0V to threshold (V_{ILD}), f = 1 MHz.

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AC Electrical Characteristics

	Parameter		$T_A = +25^{\circ}C$ $C_L = 50 \text{ pF}$			$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$ $C_{L} = 50 \text{ pF}$		Units	
Symbol		V _{CC}							
		(V)	Min	Тур	Max	Min	Max		
t _{PHL}	Propagation Delay	2.7	2.0	7.8	12.7	2.0	14.0	ns	
t _{PLH}	Data to Output	3.3 ± 0.3	2.0	6.5	9.0	2.0	9.5		
t _{PZL}	Output Enable Time	2.7	2.5	9.6	18.3	2.5	19.0	ns	
t _{PZH}		3.3 ± 0.3	2.5	8.0	13.0	2.5	13.5	115	
t _{PHZ}	Output Disable Time	2.7	1.0	10.2	20.4	1.0	21.0		
t _{PLZ}		3.3 ± 0.3	1.0	8.5	14.5	1.0	15.0	ns	
t _{OSHL}	Output to Output	2.7		1.0	1.5		1.5	20	
t _{OSLH}	Skew Data to Output (Note 9)	$\textbf{3.3}\pm\textbf{0.3}$		1.0	1.5		1.5	ns	

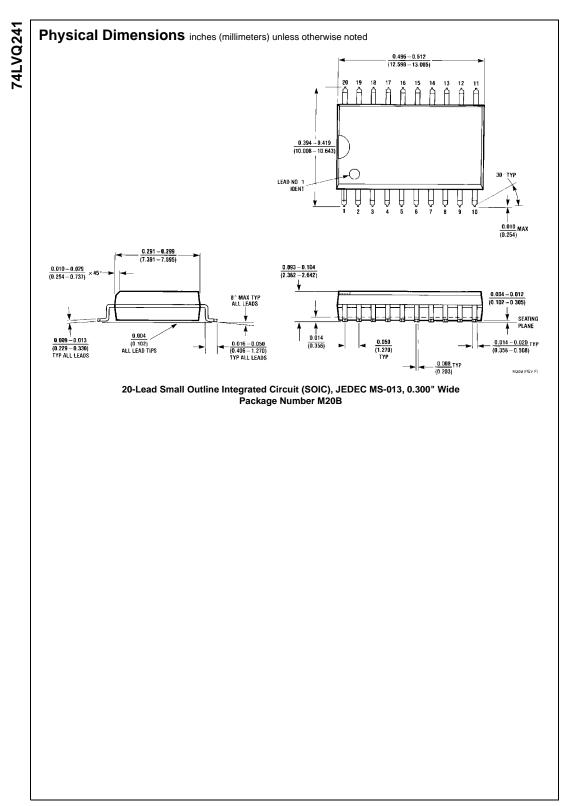
Note 9: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}). Parameter guaranteed by design.

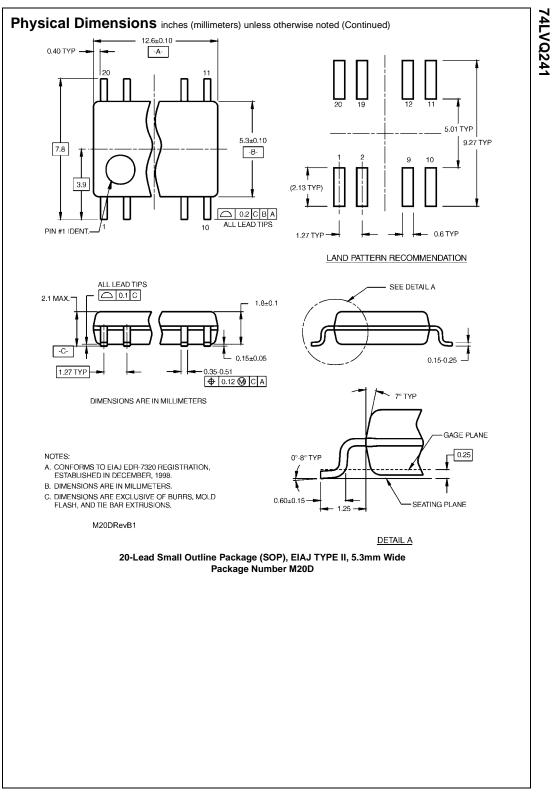
Capacitance

Symbol	Parameter	Тур	Units	Conditions
C _{IN}	Input Capacitance	4.5	pF	V _{CC} = Open
C _{PD} (Note 10)	Power Dissipation Capacitance	70	pF	$V_{CC} = 3.3V$

Note 10: C_{PD} is measured at 10 MHz.

74LVQ241





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